

One Watt High Voltage Transistor

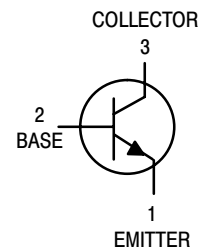
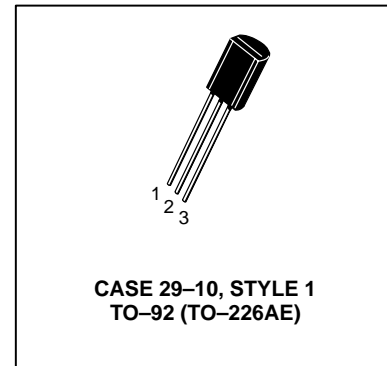
NPN Silicon

MPSW42

ON Semiconductor Preferred Device

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	300	Vdc
Collector–Base Voltage	V_{CBO}	300	Vdc
Emitter–Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	500	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	1.0 8.0	Watt mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	2.5 20	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ⁽¹⁾ ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	$V_{(BR)CEO}$	300	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 100 \mu\text{Adc}, I_E = 0$)	$V_{(BR)CBO}$	300	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 100 \mu\text{Adc}, I_C = 0$)	$V_{(BR)EBO}$	6.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 200 \text{ Vdc}, I_E = 0$)	I_{CBO}	—	0.1	μAdc
Emitter Cutoff Current ($V_{EB} = 6.0 \text{ Vdc}, I_C = 0$)	I_{EBO}	—	0.1	μAdc

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS				
DC Current Gain ($I_C = 1.0\text{ mA}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 10\text{ mA}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 30\text{ mA}$, $V_{CE} = 10\text{ Vdc}$)	h_{FE}	25 40 40	— — —	—
Collector–Emitter Saturation Voltage ($I_C = 20\text{ mA}$, $I_B = 2.0\text{ mA}$)	$V_{CE(sat)}$	—	0.5	Vdc
Base–Emitter Saturation Voltage ($I_C = 20\text{ mA}$, $I_B = 2.0\text{ mA}$)	$V_{BE(sat)}$	—	0.9	Vdc
SMALL–SIGNAL CHARACTERISTICS				
Current–Gain — Bandwidth Product ($I_C = 10\text{ mA}$, $V_{CE} = 20\text{ Vdc}$, $f = 20\text{ MHz}$)	f_T	50	—	MHz
Collector Capacitance ($V_{CB} = 20\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{cb}	—	3.0	pF

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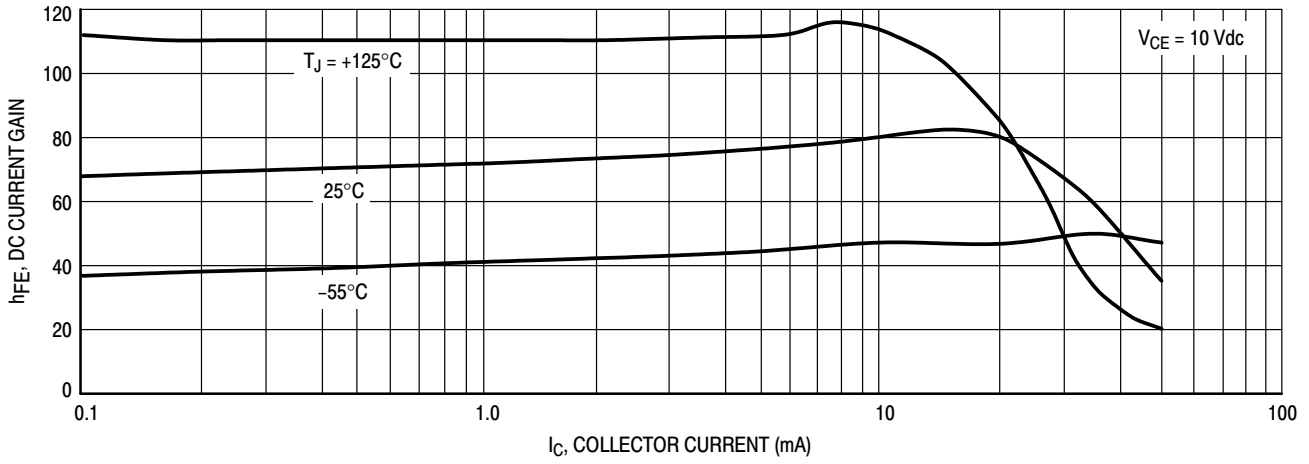


Figure 1. DC Current Gain

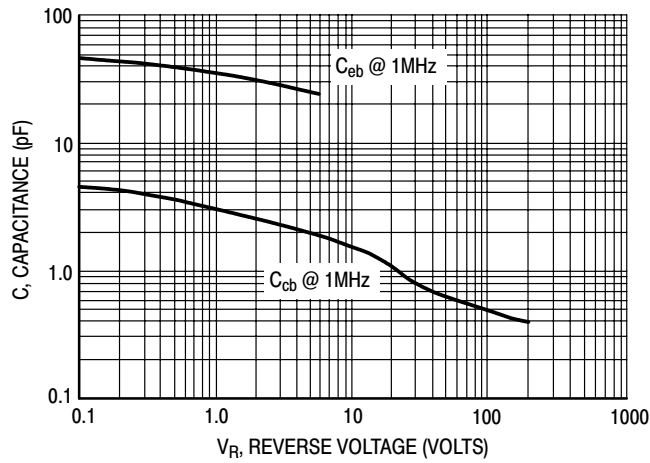


Figure 2. Capacitance

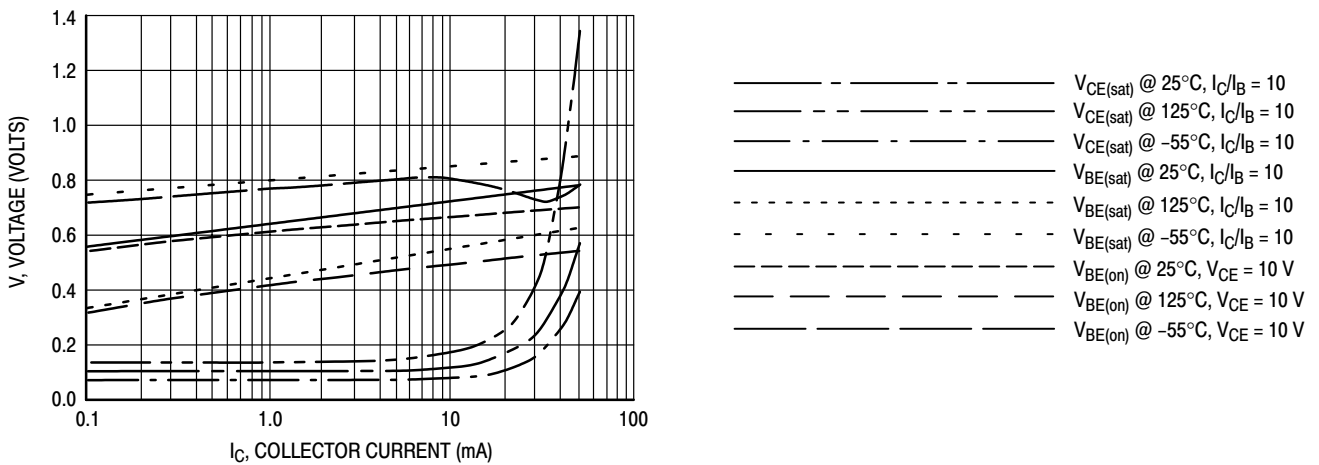


Figure 3. "ON" Voltages